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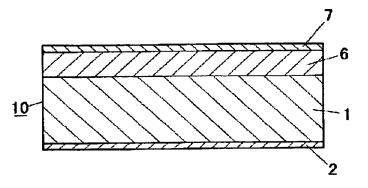
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TITLE

: ELECTRIC FIELD RADIATION

ELECTRON SOURCE AND METHOD

FOR MANUFACTURING



ABSTRACT :

PROBLEM TO BE SOLVED: To provide an electric field radiation electron source and method of fabricating it that enhances the electron emission effect with high withstand voltage.

SOLUTION: An electric field drift layer 6 is formed on the main surface of an n-type silicon substrate 1, having a surface electrode 7. An ohmic electrode 2 is formed in the inside of the silicon substrate 1. The strong electric field drift layer 6 is obtained by annealing a porous polycrystalline silicon layer formed by anode oxidizing process in an atmosphere of N2O or NO gas at 900°C for an hour. The polycrystalline layer thus obtained has high electron emission efficiency, low defect density, and high withstand voltage compared to the conventional silicon layer.

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